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| In place of PTO-1449 Form | | U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | | Complete if Known | |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) | | | | Application Number | |
| | | | | Filing Date | Herewith |
| | | | | Applicant(s) | Chien-Chao Huang |
| | | | | Art Unit | |
| | | | | Examiner Name | |
| SHEET | 1 | OF | 1 | Attorney Docket Number | 24061.150 (TSMC2003-0964) |

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| TD | AB | 6,600,170 | 07-29-2003 | Xiang |
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| Examiner's Initials | Cite No. | Foreign Patent Document (Country Code - Number - Kind) | Publication Date MM-DD-YYYY | Patentee or Applicant of Cited Document | Translation Y/N |
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| OTHER PRIOR ART | | |
|---------------------|----------|---|
| Examiner's Initials | Cite No. | Include name of the author, (in CAPITAL LETTERS) title of the article, title of the item, date, page(s), volume, issue, number(s), publisher, city/country where published |
| JD | AC | Y. C. YEO et al., "Enhanced Performance in Sub-100 nm CMOSFETs using Strained Epitaxial Silicon-Germanium", IEDM Technical Digest, December 10-13, 2000, pgs. 753-756, IEEE. |
| TD | AD | C. R. SELVAKUMAR et al., "Sige-Channel NMOSFET by Germanium Implantation", IEEE Electron Device Letters, 1991, Vol/Issue 12/8 August, pages 444-446, IEEE. |
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| Examiner Signature | | Date Considered | 10/25/05 |
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.